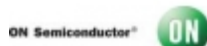
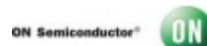
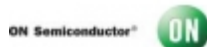


specificazioni	
Modello di prodotti	FQA11N90
fabbricante	Fairchild/ON Semiconductor
Descrizione	MOSFET N-CH 900V 11.4A TO-3P
Categoria	Prodotti a semiconduttore discreti > Transistor-FET ,
Stato parte	6465 pcs Stock
Vgs (th) (max) a Id	5V @ 250μA
Tecnologia	MOSFET (Metal Oxide)
Contenitore dispositivo fornitore	TO-3P
Serie	QFET®
Rds On (max) a Id, Vgs	960 mOhm @ 5.7A, 10V
Dissipazione di potenza (max)	300W (Tc)
imballaggio	Tube
Contenitore / involucro	TO-3P-3, SC-65-3
temperatura di esercizio	-55°C ~ 150°C (TJ)
Tipo montaggio	Through Hole
Capacità di ingresso (Ciss) (Max) @ Vds	3500pF @ 25V
Carica Gate (Qg) (Max) @ Vgs	94nC @ 10V
Tipo FET	N-Channel
Caratteristica FET	-
Tensione drain-source (Vdss)	900V
Corrente - Drain continuo (Id) @ 25 ° C	11.4A (Tc)

 FQA10N80_F109 Fairchild/ON Semiconductor MOSFET N-CH 800V 9.8A TO-3P	 FQA11N90 AMI Semiconductor / ON Semiconductor MOSFET N-CH 900V 11.4A TO-3P	 FQA11N90-F109 AMI Semiconductor / ON Semiconductor MOSFET N-CH 900V 11.4A TO-3P	 FQA11N40 FSC FQA11N40 FSC
 FQA11N90C AMI Semiconductor / ON Semiconductor MOSFET N-CH 900V 11A TO-3P	 FQA11N90C Fairchild/ON Semiconductor MOSFET N-CH 900V 11A TO-3P	 FQA11N90C Fairchild/ON Semiconductor MOSFET N-CH 900V 11A TO-3P	 FQA10N80_F109 AMI Semiconductor / ON Semiconductor MOSFET N-CH 800V 9.8A TO-3P

Di Più

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